TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

# 2SC2996

FM/AM RF, MIX, Local, IF High Frequency Amplifier Applications

- · High stability oscillation voltage on FM local oscillator
- Recommend FM/AM RF, MIX, local and IF

## Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	40	V
Collector-emitter voltage	V <sub>CEO</sub>	30	٧
Emitter-base voltage	V <sub>EBO</sub>	4	٧
Collector current	IC	50	mA
Emitter current	ΙE	-50	mA
Collector power dissipation	PC	150	wW
Junction temperature	Tj	125	°C
Storage temperature range	T <sub>stg</sub>	-55~125	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Unit: mm

1. BASE
2. EMITTER
3. COLLECTOR

2.5-0.3

1. BASE
2. EMITTER
3. COLLECTOR

JEDEC TO-236

JEITA —

TOSHIBA 2-3F1A

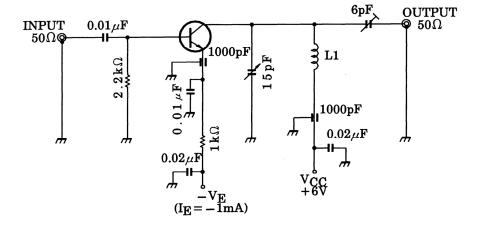
Weight: 0.012 g (typ.)

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

### **Electrical Characteristics (Ta = 25°C)**

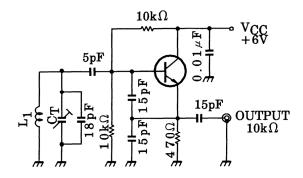
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 40 V, I <sub>E</sub> = 0	_	_	0.1	μА
Emitter cut-off current	I <sub>EBO</sub>	$V_{EB} = 4 \text{ V}, I_{C} = 0$	_	_	0.5	μА
DC current gain	h <sub>FE</sub> (Note)	V <sub>CE</sub> = 6 V, I <sub>C</sub> = 1 mA	40	_	240	
Reverse transfer capacitance	C <sub>re</sub>	V <sub>CB</sub> = 6 V, f = 1 MHz	_	0.9	1.3	pF
Transition frequency	f <sub>T</sub>	$V_{CE} = 6 \text{ V}, I_{C} = -1 \text{ mA}$	150	350	_	MHz
Collector-base time constant	C <sub>c</sub> .rbb'	$V_{CE} = 6 \text{ V}, I_{E} = -1 \text{ mA}, f = 30 \text{ MHz}$	_	15	30	ps
Noise figure	NF	$V_{CE} = 6 \text{ V}, I_{E} = -1 \text{ mA}, f = 100 \text{ MHz}$	_	4.0	_	dB
Power gain	G <sub>pe</sub>	(Figure 1)	_	15	_	dB
Oscillation output voltage	Vosc	V <sub>CE</sub> = 6 V, f = 100 MHz (Figure 2)	_	180	_	mV

Note: hFE classification R: 40~80, O: 70~140, Y: 120~240



 $L_1$ : 0.8 mm $\phi$  silver plated copper wire, 4 T, 10ID, 8 length

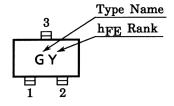
Figure 1 NF, Gpe Test Circuit



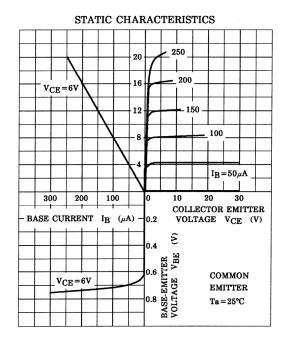
L<sub>1</sub>: 0.8 mm<sub>∮</sub> silver plated copper wire, 4 T, 10ID, 8 length

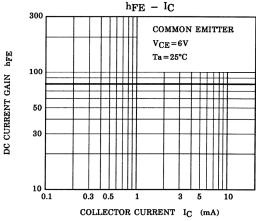
Figure 2 Vosc Test Circuit

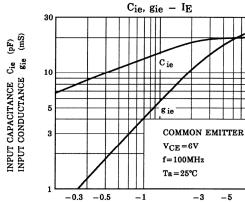
## Marking



(mA) COLLECTOR CURRENT IC

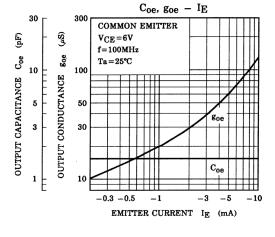


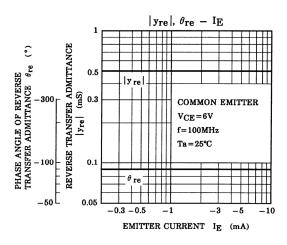




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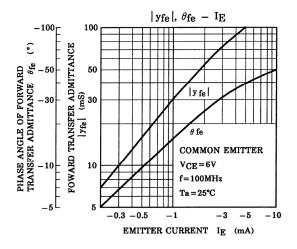
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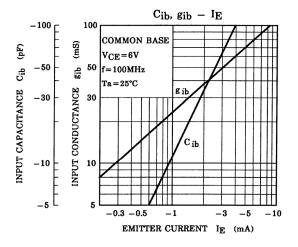


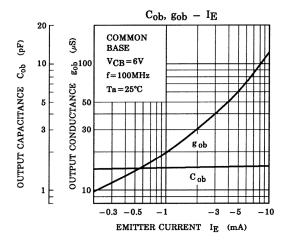


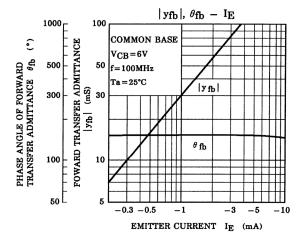
EMITTER CURRENT IE (mA)

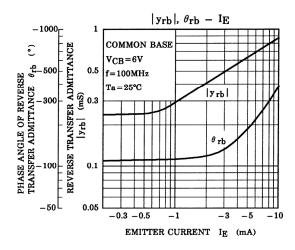
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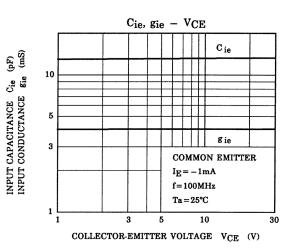


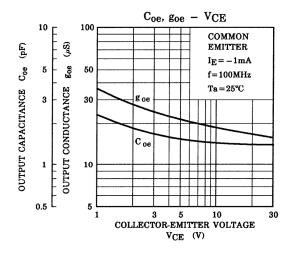


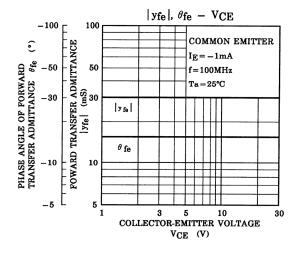


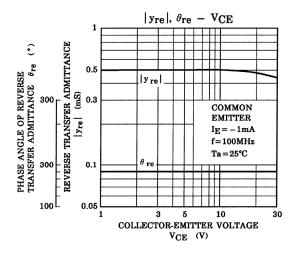


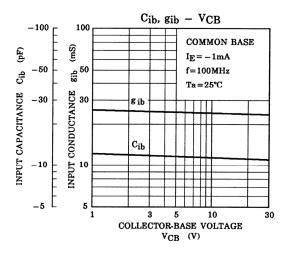


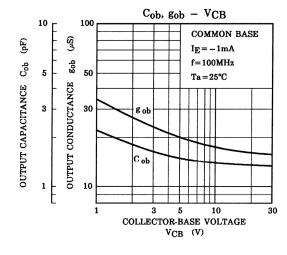


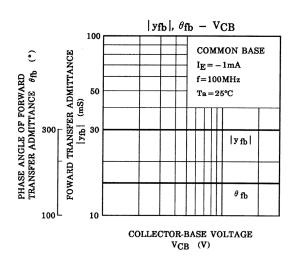


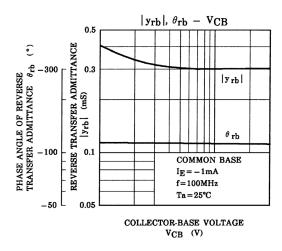


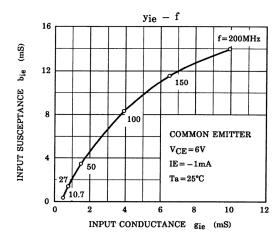


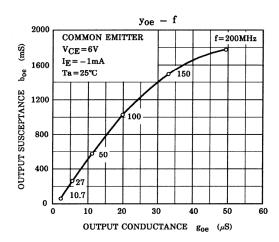


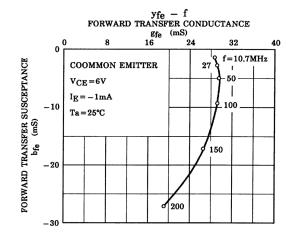


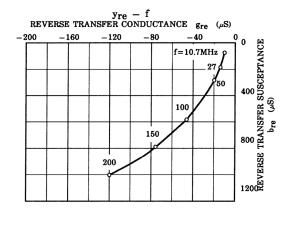


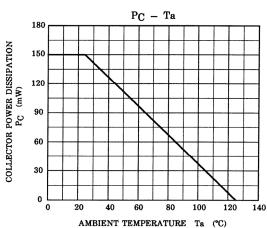












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20070701-EN GENERAL

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